## Amendments to the Claims

1 (currently amended). A hydrogen storage material <u>in the form of a film</u> comprising a first region composed primarily of an amorphous carbon containing from 0.02 to 30 atomic % of at least one metal element selected from the group consisting of Ti, Zr, Hf and Y, and a second region <u>that extends in a thickness direction of the film</u> composed primarily of an amorphous carbon, the second region having a density of from 1.4 to 2.2 g/cm<sup>3</sup> and lower than that of the first region.

2 (original). A hydrogen storage material comprising a void present in in the form of a film containing voids, wherein the film is of an amorphous carbon containing at least one metal element selected from the group consisting of Ti, Zr, Hf and Y.

3-4 (canceled).

5 (currently amended). A process for the preparation of hydrogen storage materials which comprises providing a source of carbon containing <u>pieces of</u> at least one metal element selected from the group consisting of Ti, Zr, Hf and Y, and forming a film composed of an amorphous carbon containing said metal element on the surface of a base material at a temperature of 773 K or less according to a gas phase synthesis.

6 (currently amended). A process for the preparation of hydrogen storage materials which comprises providing a source of carbon containing <u>pieces of</u> at least one metal element selected from the group consisting of Ti, Zr, Hf and Y, and forming a film composed of an amorphous carbon containing said metal element on the surface of a base material under a process gas pressure of 1.33322 Pa or more according to a sputtering process.

7 (previously presented). The hydrogen storage material of claim 2 wherein the content of the metal element is from 0.02 to 30 atomic %.

8 (currently amended). The hydrogen storage material of claim 2 which is in the form of a film, and wherein the second region or the void extends to a thickness direction of the film.

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9 (canceled).

10 (currently amended). The hydrogen storage material of claim 7 which is in the form of a film, and wherein the second region or the void extends to a thickness direction of the film.

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